

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	242	bruel.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/16 11:01
L2	85	bruel.in. and implantation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/16 11:01
L3	26	2 and etch\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/16 11:01
L4	267	(deposit\$3 near3 (Si silicon)) and ((smooth\$3 flatten\$4) near3 (Si silicon) near12 etch\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/16 11:43
L5	32	4 and (silicon adj insulator)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/16 11:15
L6	18	(deposit\$3 near3 (Si silicon)) and ((smooth\$3 flatten\$4) near3 (Si silicon) near12 (RIE ((irradiat\$3 beam) near3 etch\$3)) )	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/16 11:44
L8	2	"5650043".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/16 12:30
S1	5	((ammonium adj2 hydroxide) or "NH.sub.4OH" or "NH.sub.4 OH") near12 ((ammonium adj2 fluoride) or "NH.sub.4F" "NH.sub.4 F") near12 etch\$3 near4 (semiconductor silicon Si)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/16 11:01
S2	1721	(deposit\$3 near3 (Si silicon)) and ((smooth\$3 flatten\$4) near3 (Si silicon))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/15 22:02

S3	267	(deposit\$3 near3 (Si silicon)) and ((smooth\$3 flatten\$4) near3 (Si silicon) near12 etch\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/16 11:14
S4	101	S3 and ((wet liquid) near3 etch\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/15 22:03